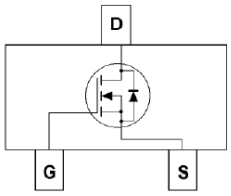
SHIKUES

IRLML2402

N-Channel Enhancement Mode MOSFET

Feature

- 30V/1A, RDS(ON) =750mΩ (MAX) @VGS = 10V. Ids = 0.60A
  RDS(ON) = 900mΩ (MAX) @VGS = 4.5V. Ids= 0.20A
- Super High dense cell design for extremely low RDS(ON) .
- Reliable and Rugged.
- SOT-23 for Surface Mount Package.



Absolute Maximum Ratings T_A=25℃ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	1	A

Electrical Characteristics T_A=25℃ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=250μA	30	-	-	V
Zero-Gate Voltage Drain Current	IDSS	VDS=24V, VGS=0V	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	VGS=20V, VDS=0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	VGS=-20V, VDS=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=250μA	1	-	-	V
Static Drain-source On-Resistance	RDS(ON)	VGS =10V, ID =0.6A	-	-	750	mΩ
		VGS =4.5V, ID =0.2A	-	-	900	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=0.23A			1.2	V